

<b>Notice of References Cited</b>	Application/Control No. 10/078,473	Applicant(s)/Patent Under Reexamination KWON, HOKI	
	Examiner Dung (Michael) T. Nguyen	Art Unit 2828	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,266,814 A	11-1993	Inata et al.	257/25
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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	N					
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	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	McDermott et al. (Growth and doping of GaAsSb via metalorganic chemical vapor deposition for InP heterojunction bipolar transistors in Appl. Phys. Lett., Vo1.68, No. 10, 4 March 1996).
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.